

NDD60N550U1

N-Channel Power MOSFET 600 V, 550 mΩ

Features

- 100% Avalanche Tested
- These Devices are Pb-Free, Halogen Free/BFR Free and are RoHS Compliant

ABSOLUTE MAXIMUM RATINGS ($T_J = 25^\circ\text{C}$ unless otherwise noted)

Parameter	Symbol	NDD	Unit
Drain-to-Source Voltage	V_{DS}	600	V
Gate-to-Source Voltage	V_{GS}	± 25	V
Continuous Drain Current $R_{\theta JC}$	I_D	$T_C = 25^\circ\text{C}$	8.2
		$T_C = 100^\circ\text{C}$	5.2
Power Dissipation – $R_{\theta JC}$	P_D	$T_C = 25^\circ\text{C}$	94
Pulsed Drain Current	I_{DM}	$t_p = 10 \mu\text{s}$	34
Operating Junction and Storage Temperature	T_J, T_{STG}	–55 to +150	$^\circ\text{C}$
Source Current (Body Diode)	I_S	8.2	A
Single Pulse Drain-to-Source Avalanche Energy ($I_D = 4 \text{ A}$)	EAS	54	mJ
Peak Diode Recovery (Note 1)	dv/dt	15	V/ns
Lead Temperature for Soldering Leads	T_L	260	$^\circ\text{C}$

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. $I_{SD} < 8.2 \text{ A}$, $di/dt \leq 400 \text{ A}/\mu\text{s}$, $V_{DS \text{ peak}} \leq V_{(BR)DSS}$, $V_{DD} = 80\% V_{(BR)DSS}$

THERMAL RESISTANCE

Parameter	Symbol	Value	Unit
Junction-to-Case (Drain) NDD60N550U1	$R_{\theta JC}$	1.3	$^\circ\text{C}/\text{W}$
Junction-to-Ambient Steady State (Note 3) NDD60N550U1	$R_{\theta JA}$	47	$^\circ\text{C}/\text{W}$
(Note 2) NDD60N550U1–1		98	
(Note 2) NDD60N550U1–35		95	

2. Insertion mounted
3. Surface mounted on FR4 board using 1" sq. pad size (Cu area = 1.127 in sq [2 oz] including traces)

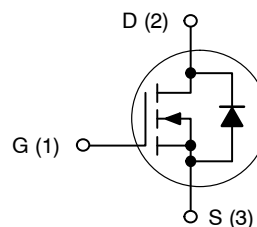


ON Semiconductor®

<http://onsemi.com>

$V_{(BR)DSS}$	$R_{DS(ON) \text{ MAX}}$
600 V	550 mΩ @ 10 V

N-Channel MOSFET



IPAK
CASE 369D
STYLE 2

DPAK
CASE 369C
STYLE 2

IPAK
CASE 369AD
STYLE 2

MARKING AND ORDERING INFORMATION

See detailed ordering and shipping information on page 3 of this data sheet.

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ELECTRICAL CHARACTERISTICS (T_J = 25°C unless otherwise noted)

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
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OFF CHARACTERISTICS

Drain-to-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0 V, I _D = 1 mA	600			V
Drain-to-Source Breakdown Voltage Temperature Coefficient	V _{(BR)DSS} /T _J			540		mV/°C
Drain-to-Source Leakage Current	I _{DSS}	V _{DS} = 600 V, V _{GS} = 0 V	T _J = 25°C		1	μA
			T _J = 125°C		100	
Gate-to-Source Leakage Current	I _{GSS}	V _{GS} = ±25 V			±100	nA

ON CHARACTERISTICS (Note 4)

Gate Threshold Voltage	V _{GS(TH)}	V _{DS} = V _{GS} , I _D = 250 μA	2	3.2	4	V
Negative Threshold Temperature Coefficient	V _{GS(TH)} /T _J	Reference to 25°C, I _D = 250 μA		7.6		mV/°C
Static Drain-to-Source On Resistance	R _{DS(on)}	V _{GS} = 10 V, I _D = 4 A		510	550	mΩ
Forward Transconductance	g _{FS}	V _{DS} = 15 V, I _D = 4 A		7.0		S

DYNAMIC CHARACTERISTICS

Input Capacitance	C _{iss}	V _{DS} = 50 V, V _{GS} = 0 V, f = 1 MHz		540		pF
Output Capacitance	C _{oss}			33		
Reverse Transfer Capacitance	C _{rss}			1.6		
Effective output capacitance, energy related (Note 6)	C _{o(er)}	V _{GS} = 0 V, V _{DS} = 0 to 480 V		24		
Effective output capacitance, time related (Note 7)	C _{o(tr)}	I _D = constant, V _{GS} = 0 V, V _{DS} = 0 to 480 V		84		
Total Gate Charge	Q _g	V _{DS} = 300 V, I _D = 9.5 A, V _{GS} = 10 V		18		nC
Gate-to-Source Charge	Q _{gs}			3.4		
Gate-to-Drain Charge	Q _{gd}			8.7		
Plateau Voltage	V _{GP}			5.4		V
Gate Resistance	R _g			5.5		Ω

RESISTIVE SWITCHING CHARACTERISTICS (Note 5)

Turn-on Delay Time	t _{d(on)}	V _{DD} = 300 V, I _D = 9.5 A, V _{GS} = 10 V, R _G = 0 Ω		8		ns
Rise Time	t _r			14		
Turn-off Delay Time	t _{d(off)}			20		
Fall Time	t _f			17		

SOURCE-DRAIN DIODE CHARACTERISTICS

Diode Forward Voltage	V _{SD}	I _S = 8.2 A, V _{GS} = 0 V	T _J = 25°C		0.9	1.3	V
			T _J = 100°C		0.82		
Reverse Recovery Time	t _{rr}	V _{GS} = 0 V, V _{DD} = 30 V, I _S = 9.5 A, dI/dt = 100 A/μs		290		ns	
Charge Time	t _a			160			
Discharge Time	t _b			130			
Reverse Recovery Charge	Q _{rr}			2.6			μC

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

4. Pulse Width ≤ 300 μs, Duty Cycle ≤ 2%.

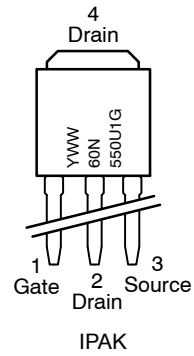
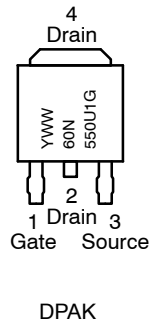
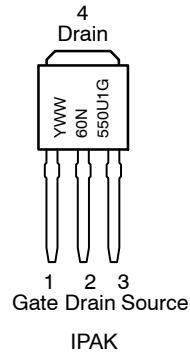
5. Switching characteristics are independent of operating junction temperatures.

6. C_{o(er)} is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{(BR)DSS}

7. C_{o(tr)} is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{(BR)DSS}

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MARKING DIAGRAMS



Y = Year
WW = Work Week
G = Pb-Free Package

ORDERING INFORMATION

Device	Package	Shipping [†]
NDD60N550U1-1G	IPAK (Pb-Free, Halogen-Free)	75 Units / Rail
NDD60N550U1-35G	IPAK (Pb-Free, Halogen-Free)	75 Units / Rail
NDD60N550U1T4G	DPAK (Pb-Free, Halogen-Free)	2500 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

TYPICAL CHARACTERISTICS

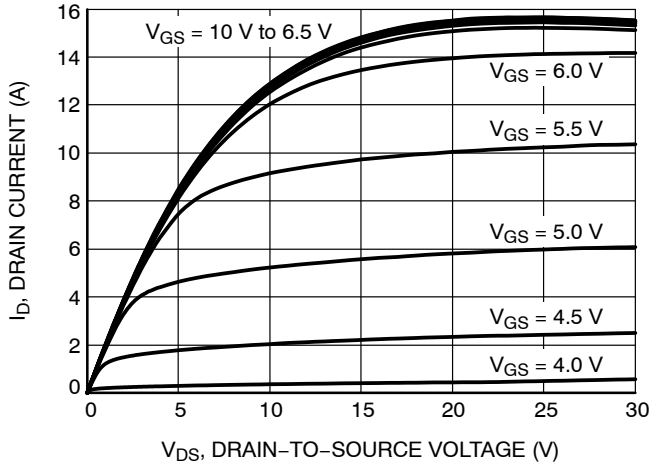


Figure 1. On-Region Characteristics

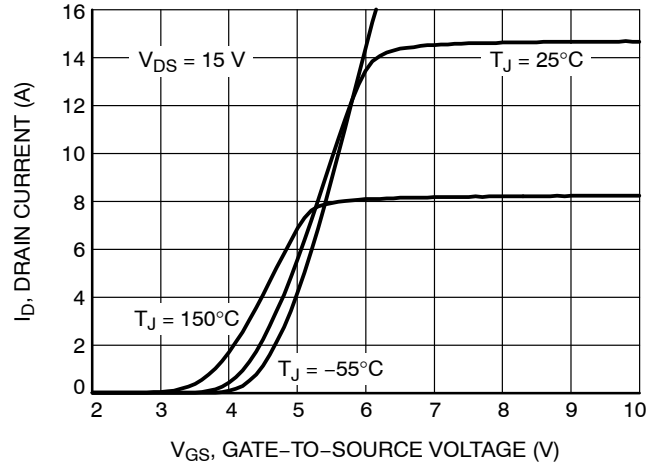


Figure 2. Transfer Characteristics

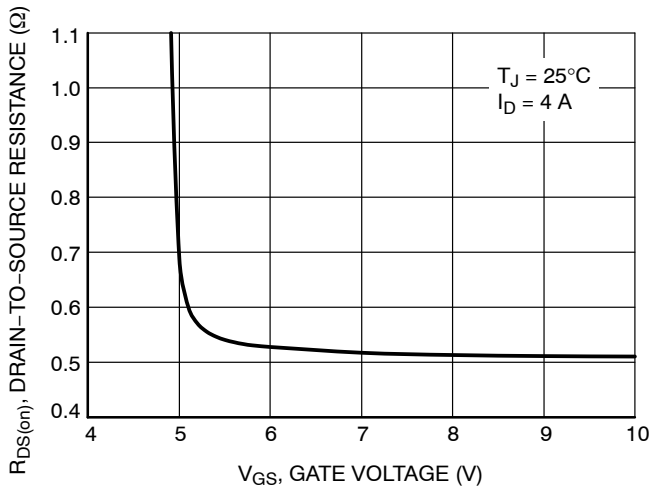


Figure 3. On-Resistance vs. Gate-to-Source Voltage

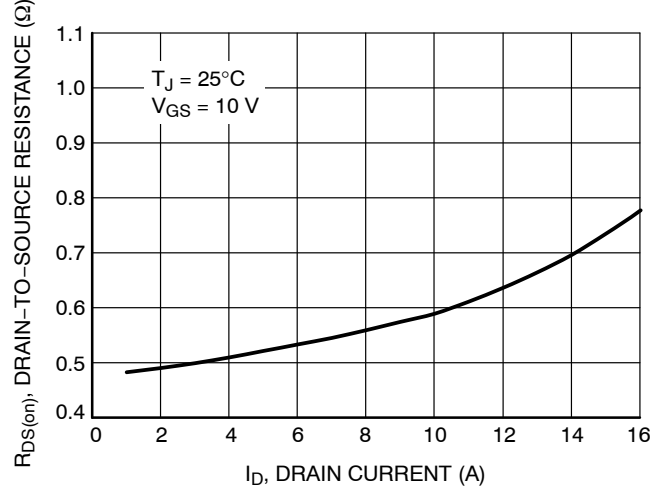


Figure 4. On-Resistance vs. Drain Current and Gate Voltage

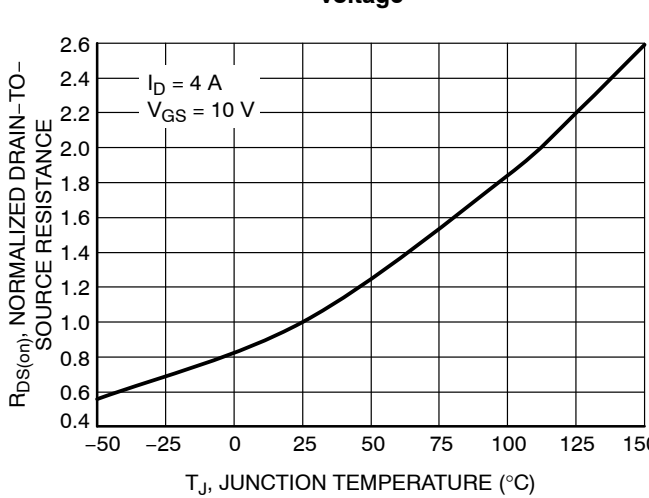


Figure 5. On-Resistance Variation with Temperature

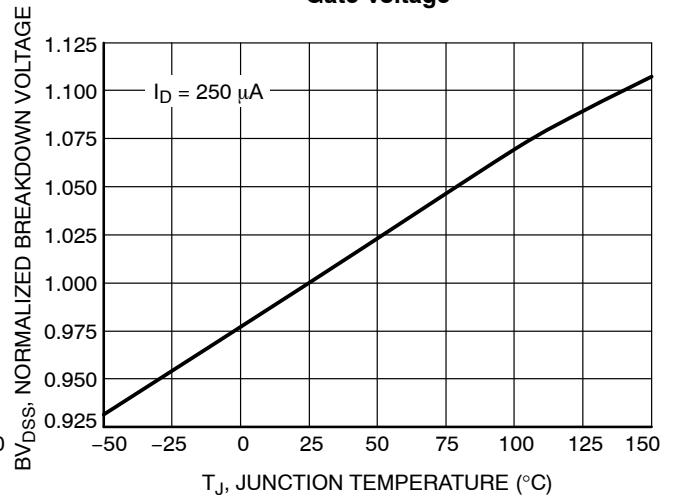


Figure 6. Breakdown Voltage Variation with Temperature

TYPICAL CHARACTERISTICS

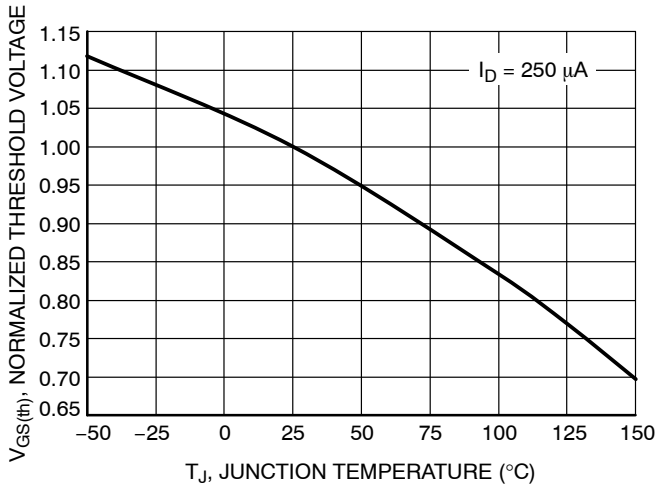


Figure 7. Threshold Voltage Variation with Temperature

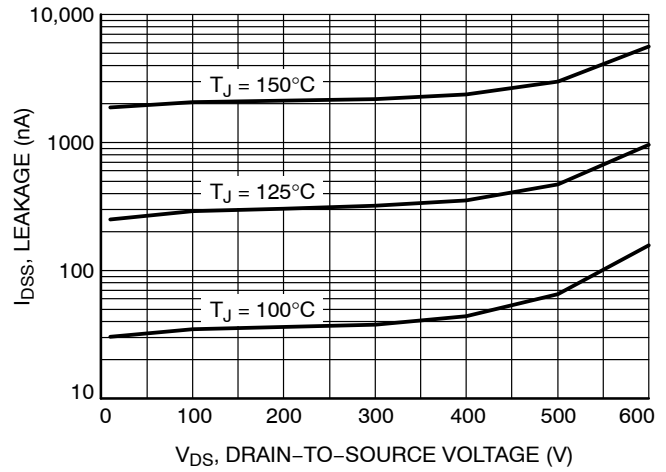


Figure 8. Drain-to-Source Leakage Current vs. Voltage

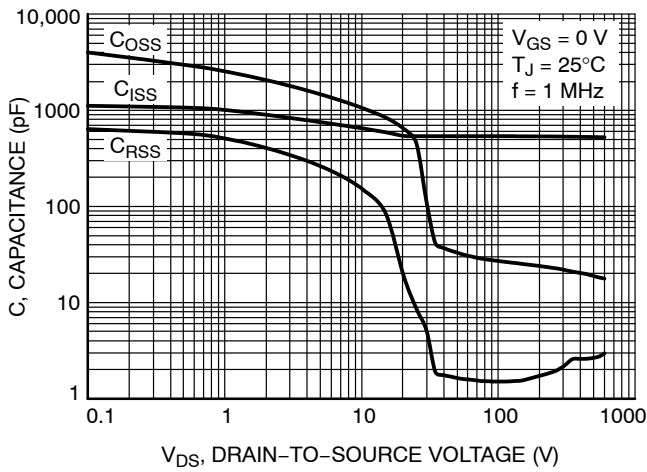


Figure 9. Capacitance Variation

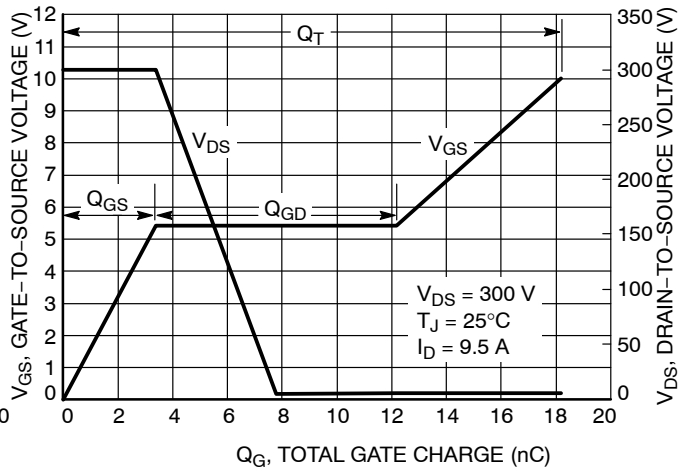


Figure 10. Gate-to-Source and Drain-to-Source Voltage vs. Total Charge

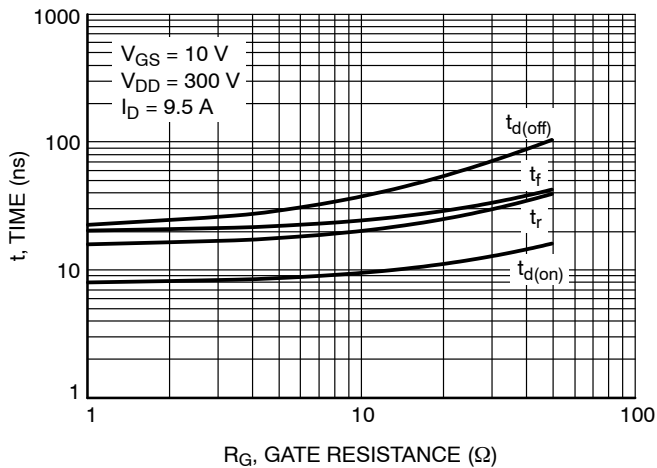


Figure 11. Resistive Switching Time Variation vs. Gate Resistance

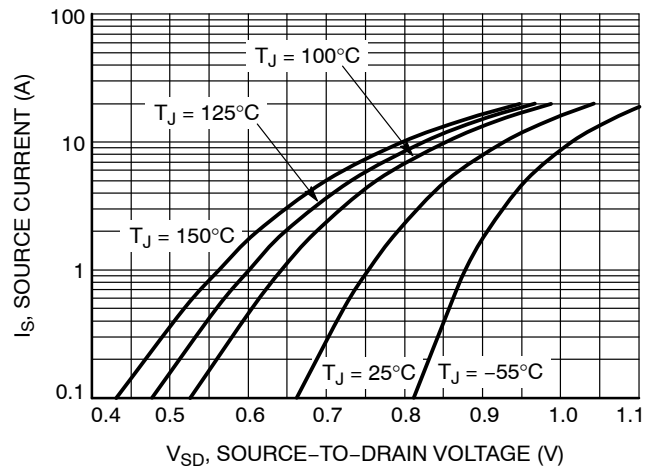


Figure 12. Diode Forward Voltage vs. Current

TYPICAL CHARACTERISTICS

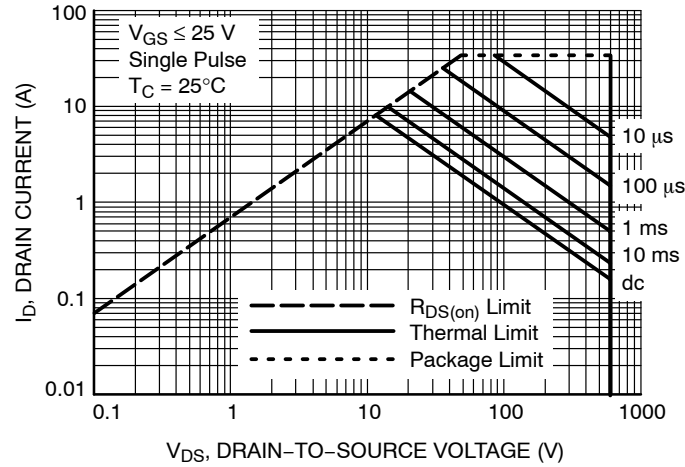


Figure 13. Maximum Rated Forward Biased Safe Operating Area

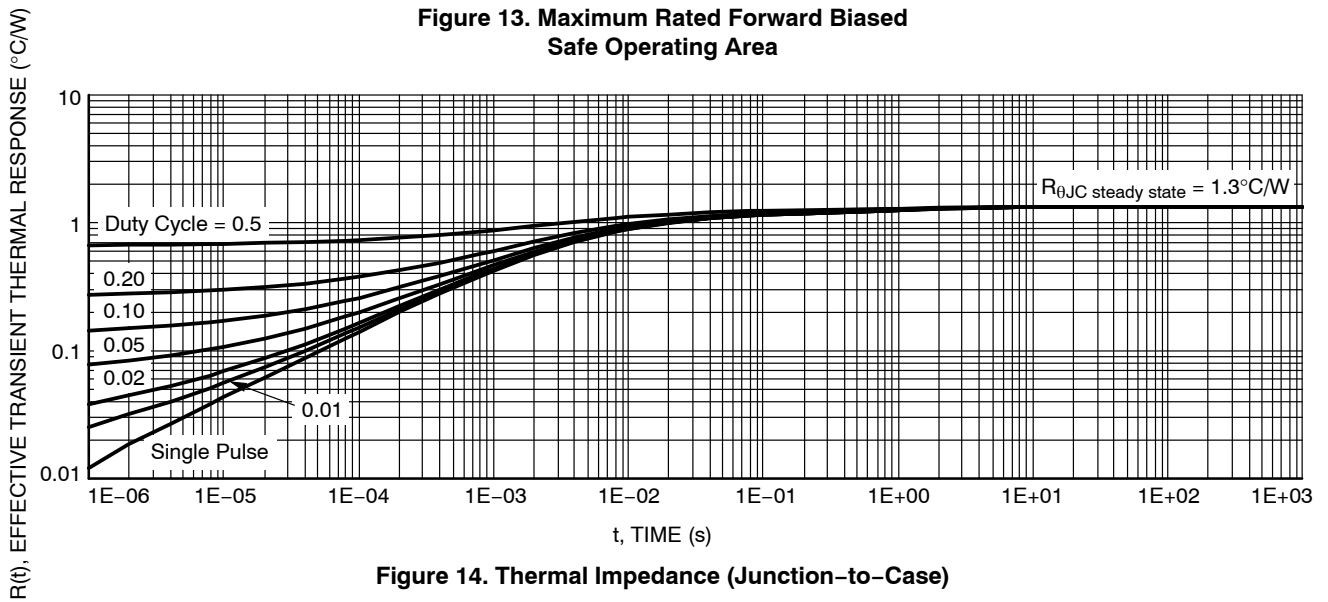
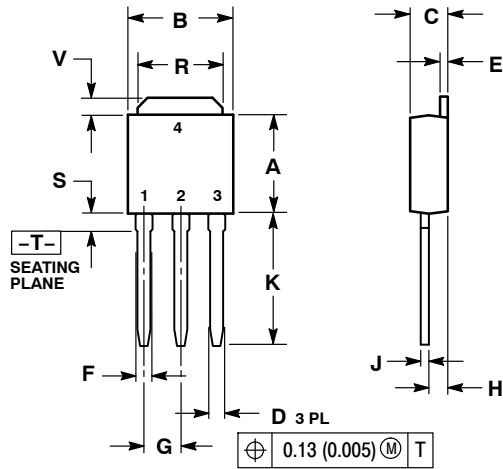


Figure 14. Thermal Impedance (Junction-to-Case)

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PACKAGE DIMENSIONS

IPAK CASE 369D ISSUE C



NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

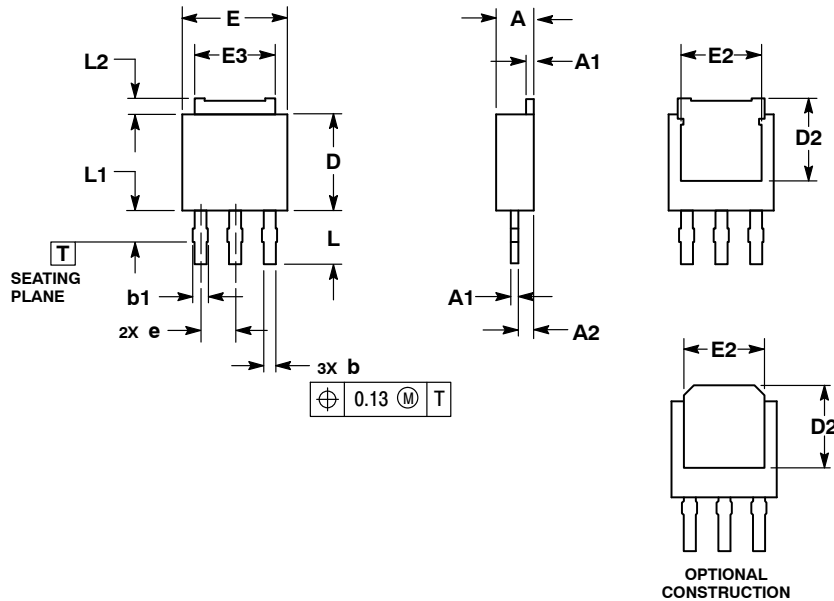
DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.235	0.245	5.97	6.35
B	0.250	0.265	6.35	6.73
C	0.086	0.094	2.19	2.38
D	0.027	0.035	0.69	0.88
E	0.018	0.023	0.46	0.58
F	0.037	0.045	0.94	1.14
G	0.090 BSC		2.29 BSC	
H	0.034	0.040	0.87	1.01
J	0.018	0.023	0.46	0.58
K	0.350	0.380	8.89	9.65
R	0.180	0.215	4.45	5.45
S	0.025	0.040	0.63	1.01
V	0.035	0.050	0.89	1.27
Z	0.155	---	3.93	---

STYLE 2:

- PIN 1. GATE
- DRAIN
- SOURCE
- DRAIN

3.5 MM IPAK, STRAIGHT LEAD

CASE 369AD ISSUE B



NOTES:

1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. DIMENSION b APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.15 AND 0.30mm FROM TERMINAL TIP.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD GATE OR MOLD FLASH.

DIM	MILLIMETERS	
	MIN	MAX
A	2.19	2.38
A1	0.46	0.60
A2	0.87	1.10
b	0.69	0.89
b1	0.77	1.10
D	5.97	6.22
D2	4.80	---
E	6.35	6.73
E2	4.57	5.45
E3	4.45	5.46
e	2.28 BSC	
L	3.40	3.60
L1	---	2.10
L2	0.89	1.27

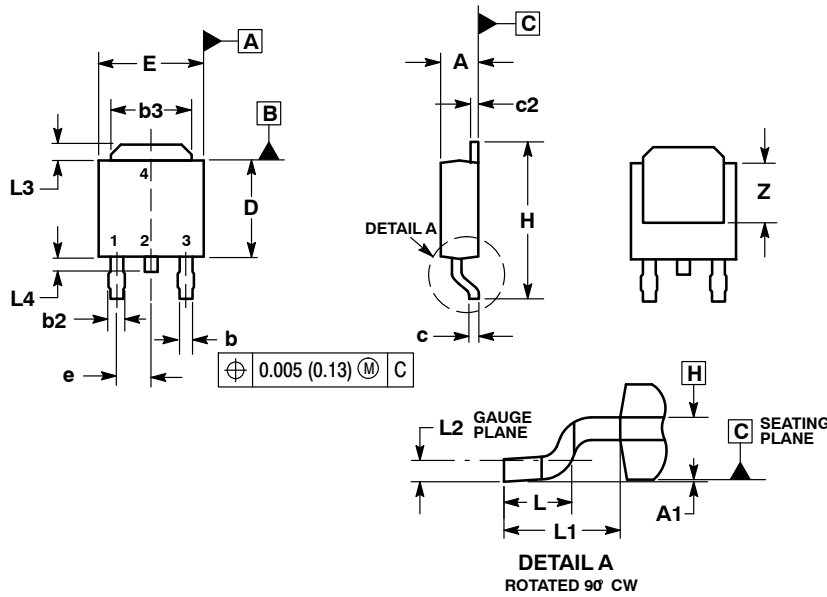
STYLE 2:

- PIN 1. GATE
- DRAIN
- SOURCE
- DRAIN

NDD60N550U1

PACKAGE DIMENSIONS

DPAK (SINGLE GAUGE) CASE 369C ISSUE D



NOTES:

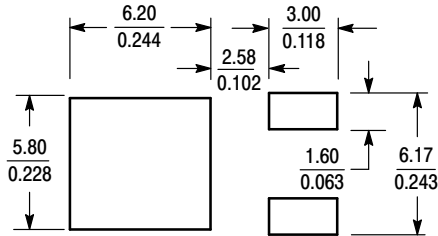
1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
2. CONTROLLING DIMENSION: INCHES.
3. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS b3, L3 and Z.
4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR BURRS. MOLD FLASH, PROTRUSIONS, OR GATE BURRS SHALL NOT EXCEED 0.006 INCHES PER SIDE.
5. DIMENSIONS D AND E ARE DETERMINED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
6. DATUMS A AND B ARE DETERMINED AT DATUM PLANE H.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.086	0.094	2.18	2.38
A1	0.000	0.005	0.00	0.13
b	0.025	0.035	0.63	0.89
b2	0.030	0.045	0.76	1.14
b3	0.180	0.215	4.57	5.46
c	0.018	0.024	0.46	0.61
c2	0.018	0.024	0.46	0.61
D	0.235	0.245	5.97	6.22
E	0.250	0.265	6.35	6.73
e	0.090	BSC	2.29	BSC
H	0.370	0.410	9.40	10.41
L	0.055	0.070	1.40	1.78
L1	0.108	REF	2.74	REF
L2	0.020	BSC	0.51	BSC
L3	0.035	0.050	0.89	1.27
L4	---	0.040	---	1.01
Z	0.155	---	3.93	---

STYLE 2:

1. GATE
2. DRAIN
3. SOURCE
4. DRAIN

SOLDERING FOOTPRINT*



SCALE 3:1 (mm/inches)

*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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